

September 2009

# H11AA1M, H11AA2M, H11AA3M, H11AA4M AC Input/Phototransistor Optocouplers

#### **Features**

- Bi-polar emitter input
- Built-in reverse polarity input protection
- Underwriters Laboratory (UL) recognized File #E90700, Volume 2
- VDE approved File #102497 (ordering option 'V')

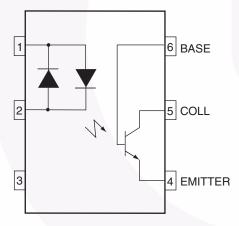
#### **Applications**

- AC line monitor
- Unknown polarity DC sensor
- Telephone line interface

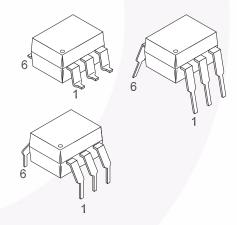
## **Description**

The H11AAXM series consists of two gallium-arsenide infrared emitting diodes connected in inverse parallel driving a single silicon phototransistor output.

#### **Schematic**



## **Package Outlines**



**Absolute Maximum Ratings** ( $T_A = 25^{\circ}C$  Unless otherwise specified) Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Device	Value	Units
TOTAL DEVIC	E			
T <sub>STG</sub>	Storage Temperature	All	-40 to +150	°C
T <sub>OPR</sub>	Operating Temperature	All	-40 to +100	°C
T <sub>SOL</sub>	Lead Solder Temperature	All	260 for 10 sec	°C
$P_{D}$	Total Device Power Dissipation	All	250	mW
	Derate Linearly From 25°C		2.94	mW/°C
EMITTER				
IF	Continuous Forward Current	All	60	mA
I <sub>F</sub> (pk)	Forward Current – Peak (1µs pulse, 300 pps)	All	±1.0	А
P <sub>D</sub>	LED Power Dissipation	All	120	mW
	Derate Linearly From 25°C		1.41	mW/°C
DETECTOR				
I <sub>C</sub>	Continuous Collector Current	All	50	mA
$P_{D}$	Detector Power Dissipation	All	150	mW
	Derate linearity from 25°C		1.76	mW/°C

# **Electrical Characteristics** ( $T_A = 25$ °C Unless otherwise specified.)

#### **Individual Component Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Тур.*	Max.	Unit
EMITTER	1	1	1	'			
V <sub>F</sub>	Input Forward Voltage	$I_F = \pm 10 \text{mA}$	All		1.17	1.5	V
CJ	Capacitance	V <sub>F</sub> = 0 V, f = 1.0MHz	All		80		pF
DETECTO	R						
BV <sub>CEO</sub>	Breakdown Voltage Collector to Emitter	$I_C = 1.0 \text{mA}, I_F = 0$	All	30	100		V
BV <sub>CBO</sub>	Collector to Base	$I_C = 100 \mu A, I_F = 0$	All	70	120		V
BV <sub>EBO</sub>	Emitter to Base	$I_E = 100 \mu A, I_F = 0$	All	5	10		V
BV <sub>ECO</sub>	Emitter to Collector	$I_E = 100 \mu A, I_F = 0$	All	7	10		V
I <sub>CEO</sub>	Leakage Current Collector to Emitter	$V_{CE} = 10 \text{ V}, I_F = 0$	H11AA1M H11AA3M H11AA4M		1	50	nA
			H11AA2M	\ \	1	200	1
C <sub>CE</sub>	Capacitance Collector to Emitter	V <sub>CE</sub> = 0, f = 1MHz	All		10		pF
C <sub>CB</sub>	Collector to Base	$V_{CB} = 0$ , $f = 1MHz$	All		80		pF
C <sub>EB</sub>	Emitter to Base	V <sub>EB</sub> = 0, f = 1MHz	All		15		pF

<sup>\*</sup>Typical values at T<sub>A</sub> = 25°C

#### **Transfer Characteristics**

Symbol	Characteristics	Test Conditions	Device	Min.	Тур.*	Max.	Units
CTR <sub>CE</sub>	Current Transfer Ratio,	$I_F = \pm 10 \text{mA}, V_{CE} = 10 \text{V}$	H11AA4M	100			%
	Collector to Emitter	H11AA3M	50				
			H11AA1M	20			
			H11AA2M	10			
	Current Transfer Ratio, Symmetry	$I_F = \pm 10 \text{mA}, V_{CE} = 10 \text{V}$ (Figure 11)	All	.33		3.0	
V <sub>CE(SAT)</sub>	Saturation Voltage, Collector to Emitter	$I_F = \pm 10$ mA, $I_{CE} = 0.5$ mA	All			.40	V

#### **Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Units
C <sub>I-O</sub>	Package Capacitance Input/Output	V <sub>I-O</sub> = 0, f = 1MHz		0.7		pF
V <sub>ISO</sub>	Isolation Voltage	f = 60Hz, t = 1 sec.	7500			Vac(pk)
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 VDC	10 <sup>11</sup>			Ω

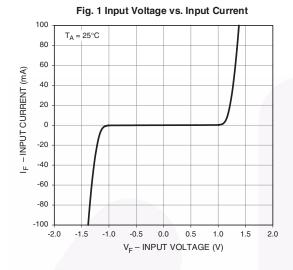
<sup>\*</sup>Typical values at  $T_A = 25$ °C

# **Safety and Insulation Ratings**

As per IEC 60747-5-2, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I-IV		
	For Rated Main voltage < 300Vrms		I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V <sub>PR</sub>	Input to Output Test Voltage, Method b, V <sub>IORM</sub> x 1.875 = V <sub>PR</sub> , 100% Production Test with tm = 1 sec, Partial Discharge < 5pC	1594			V <sub>peak</sub>
	Input to Output Test Voltage, Method a, V <sub>IORM</sub> x 1.5 = V <sub>PR</sub> , Type and Sample Test with tm = 60 sec, Partial Discharge < 5pC	1275			V <sub>peak</sub>
V <sub>IORM</sub>	Max. Working Insulation Voltage	850			V <sub>peak</sub>
$V_{IOTM}$	Highest Allowable Over Voltage	6000			V <sub>peak</sub>
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at Ts, V <sub>IO</sub> = 500V	10 <sup>9</sup>			Ω

## **Typical Performance Characteristics**



1.0 NORWALIZED OTR 0.8 0.8 0.4 0.4 0.4

1.4

12

0.2

0.0

 $T_A = 25^{\circ}C$ 

 $V_{CE} = 5V$ 

Fig. 2 Normalized CTR vs. Forward Current

Normalized to I<sub>F</sub> = 10mA

Fig. 3 Normalized CTR vs. Ambient Temperature

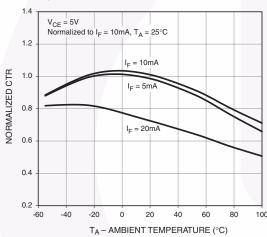


Fig. 4 CTR vs. RBE (Unsaturated)

IF - FORWARD CURRENT (mA)

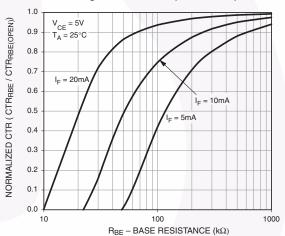


Fig. 5 CTR vs. RBE (Saturated)

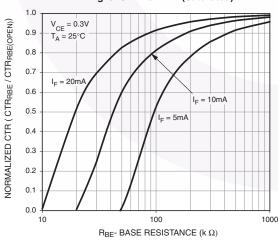
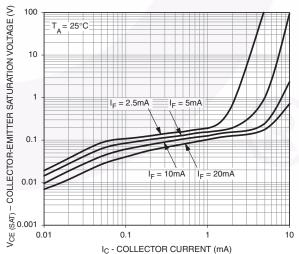
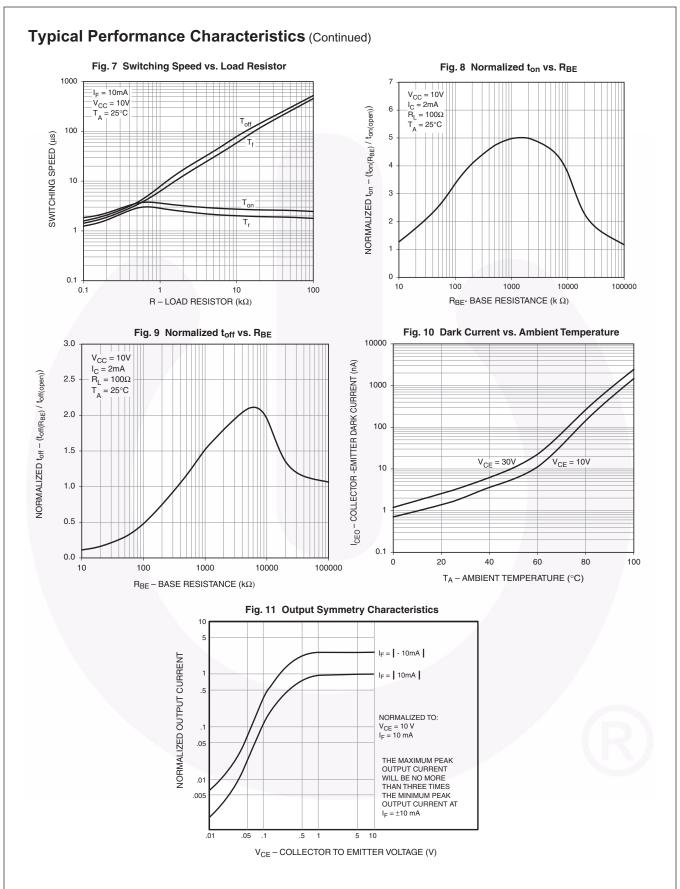


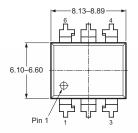
Fig. 6 Collector-Emitter Saturation Voltage vs Collector Current

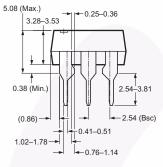


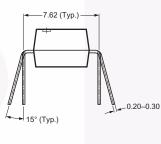


# **Package Dimensions**

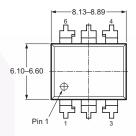
#### **Through Hole**

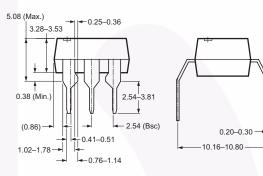




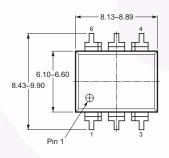


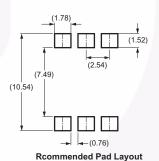
#### 0.4" Lead Spacing

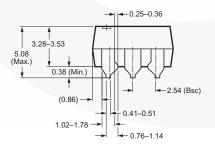


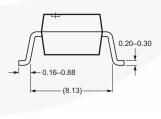


#### **Surface Mount**







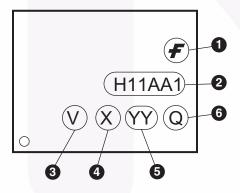


**Note:** All dimensions in mm.

# **Ordering Information**

Option	Order Entry Identifier (Example)	Description		
No option	H11AA1M	Standard Through Hole Device		
S	H11AA1SM	Surface Mount Lead Bend		
SR2 H11AA1SR2M		Surface Mount; Tape and Reel		
Т	T H11AA1TM 0.4" Lead Spacing			
V	H11AA1VM	VDE 0884		
TV	H11AA1TVM	VDE 0884, 0.4" Lead Spacing		
SV	H11AA1SVM	VDE 0884, Surface Mount		
SR2V H11AA1SR2VM VDE 0		VDE 0884, Surface Mount, Tape and Reel		

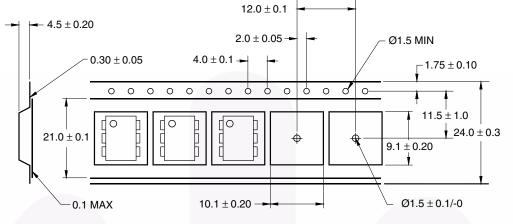
# **Marking Information**



Definiti	Definitions				
1	Fairchild logo				
2	Device number				
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)				
4	One digit year code, e.g., '3'				
5	Two digit work week ranging from '01' to '53'				
6	Assembly package code				

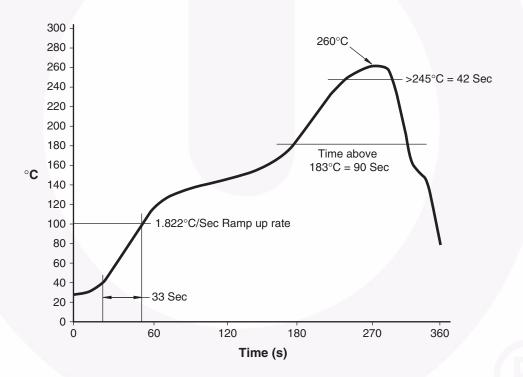
\*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

# **Carrier Tape Specification**



User Direction of Feed -----

#### **Reflow Profile**







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Scinnion of Terms					
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